XN04116 (XN4116)

Silicon PNP epitaxial planar type

For switching/digital circuits

■ Features

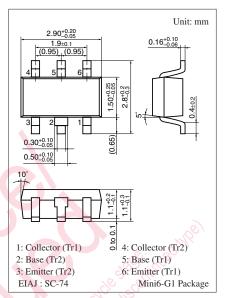
- Two elements incorporated into one package (Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

■ Basic Part Number

• UNR2116 (UN2116) × 2

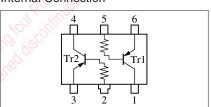
■ Absolute Maximum Ratings $T_a = 25$ °C

| Parameter | Symbol | Rating | Unit | |
|---------------------------------------|------------------|-------------|------|--|
| Collector-base voltage (Emitter open) | V _{CBO} | -50 | V | |
| Collector-emitter voltage (Base open) | V _{CEO} | -50 | V | |
| Collector current | I_C | -100 | mA | |
| Total power dissipation | P _T | 300 | mW | |
| Junction temperature | T_j | 150 | °C | |
| Storage temperature | T _{stg} | -55 to +150 | °C | |



Marking Symbol: 6U

Internal Connection

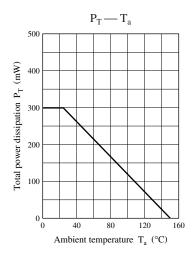


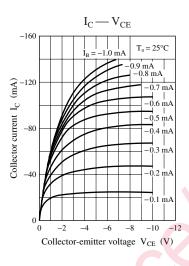
■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

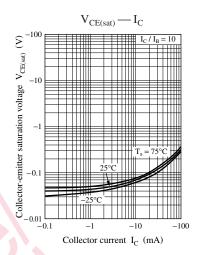
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--|----------------------|--|------|-----|--------|------|
| Collector-base voltage (Emitter open) | V_{CBO} | $I_C = -10 \mu\text{A}, I_E = 0$ | -50 | | | V |
| Collector-emitter voltage (Base open) | V _{CEO} | $I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$ | -50 | | | V |
| Collector-base cutoff current (Emitter open) | I _{CBO} | $V_{CB} = -50 \text{ V}, I_E = 0$ | | | - 0.1 | μΑ |
| Collector-emitter cutoff current (Base open) | I_{CEO} | $V_{CE} = -50 \text{ V}, I_{B} = 0$ | | | - 0.5 | μΑ |
| Emitter-base cutoff current (Collector open) | I_{EBO} | $V_{EB} = -6 \text{ V}, I_C = 0$ | | | - 0.01 | mA |
| Forward current transfer ratio | $h_{\rm FE}$ | $V_{CE} = -10 \text{ V}, I_{C} = -5 \text{ mA}$ | 160 | | 460 | _ |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_C = -10 \text{ mA}, I_B = -0.3 \text{ mA}$ | | | - 0.25 | V |
| Output voltage high-level | V _{OH} | $V_{CC} = -5 \text{ V}, V_B = -0.5 \text{ V}, R_L = 1 \text{ k}\Omega$ | -4.9 | | | V |
| Output voltage low-level | V _{OL} | $V_{CC} = -5 \text{ V}, V_B = -2.5 \text{ V}, R_L = 1 \text{ k}\Omega$ | | | - 0.2 | V |
| Input resistance | R_1 | | -30% | 4.7 | +30% | kΩ |
| Transition frequency | f_T | $V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$ | | 80 | | MHz |

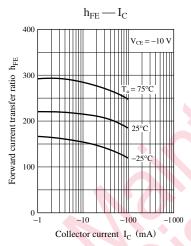
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

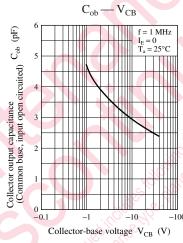
Note) The part number in the parenthesis shows conventional part number.

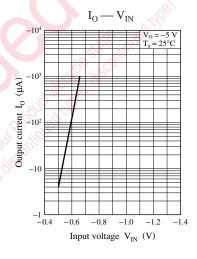


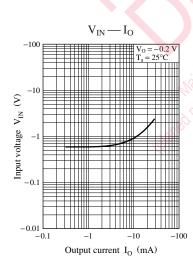












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